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1. **Electrical characteristics of novel hafnium oxide film**
Ng, K.L.; Zhan, N.; Poon, M.C.; Kok, C.W.; Chan, M.; Wong, H.;
Electron Devices Meeting, 2002. Proceedings. 2002 IEEE Hong Kong
22 June 2002 Page(s):51 - 54
IEEE CNF
2. **Characteristics of high quality hafnium oxide gate dielectric**
Zhan, N.; Ng, K.L.; Poon, M.C.; Kok, C.W.; Chan, M.; Wong, H.;
Electron Devices Meeting, 2002. Proceedings. 2002 IEEE Hong Kong
22 June 2002 Page(s):43 - 46
IEEE CNF
3. **Total-dose radiation response of hafnium-silicate capacitors**
Felix, J.A.; Fleetwood, D.M.; Schrimpf, R.D.; Hong, J.G.; Lucovsky, G.; Schwank, J.R.; Shaneyfelt, M.R.;
Nuclear Science, IEEE Transactions on
Volume 49, Issue 6, Dec. 2002 Page(s):3191 - 3196
IEEE JNL
4. **Physical characterization of high-k gate dielectric film systems processed by RTA and spike anneal**
Lyaaght, P.S.; Foran, B.; Bersuker, G.; Tichy, R.; Larson, L.; Murto, R.W.; Huff, H.R.;
Advanced Thermal Processing of Semiconductors, 2002. RTP 2002. 10th IEEE International Conference of
25-27 Sept. 2002 Page(s):93 - 98
IEEE CNF
5. **Characterization of hafnium and zirconium silicate films fabricated by plasma-enhanced chemical vapor deposition**
Kato, H.; Nango, T.; Miyagawa, T.; Katagiri, T.; Ohki, Y.;
Gate Insulator, 2001. IWGI 2001. Extended Abstracts of International Workshop on
1-2 Nov. 2001 Page(s):166 - 169
IEEE CNF
6. **Enhanced tunnel magnetoresistance by Hf layer insertion in the tunnel barriers**
Park, B.G.; Lee, T.D.;
Magnetics Conference, 2002. INTERMAG Europe 2002. Digest of Technical Papers. 2002 IEEE International
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IEEE CNF
7. **Additional scattering effects for mobility degradation in Hf-silicate gate MISFETs**
Yamaguchi, T.; Iijima, R.; Ino, T.; Nishiyama, A.; Satake, H.; Fukushima, N.;
Electron Devices Meeting, 2002. IEDM '02. Digest. International
8-11 Dec. 2002 Page(s):621 - 624
IEEE CNF
8. **Low temperature deposition of hafnium silicate gate dielectrics for TFTs on plastic substrates**
Gnade, B.E.; Pant, G.; Panchaipetch, P.; Wallace, R.M.;
Lasers and Electro-Optics Society, 2002. LEOS 2002. The 15th Annual Meeting of the IEEE
Volume 1, 10-14 Nov. 2002 Page(s):305 - 306 vol.1
IEEE CNF

IEEE CNF

18. Fabrication of hafnium silicate films by plasma-enhanced chemical vapor deposition

Kato, H.; Nango, T.; Miyagawa, T.; Katagiri, T.; Ohki, Y.; Kwang Soo Seol; Takiyama, M.;
Electrical Insulating Materials, 2001. (ISEIM 2001). Proceedings of 2001 International Symposium on
19-22 Nov. 2001 Page(s):483 - 486

IEEE CNF

19. Effects of interface oxide layer on HfO_2 gate dielectrics [MISFETS]

Morisaki, Y.; Sugita, Y.; Irino, K.; Aoyama, T.;
Gate Insulator, 2001. IWGI 2001. Extended Abstracts of International Workshop on
1-2 Nov. 2001 Page(s):184 - 187

IEEE CNF

20. Characterization of materials critical to high-speed silicon devices using secondary ion mass spectrometry

Magee, C.W.;
Junction Technology, 2002. IWJT. Extended Abstracts of the Third International Workshop on
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IEEE CNF

21. Polarity dependent reliability of advanced MOSFET using MOCVD nitrided Hf-silicate high-k gate dielectric

Zhang, J.; Zhao, E.; Xiang, Q.; Chan, J.; Jeon, J.; Goo, J.-S.; Marathe, A.; Ogle, B.; Lin, M.-R.; Taylor, K.;
Integrated Reliability Workshop Final Report, 2002. IEEE International
21-24 Oct. 2002 Page(s):92 - 95

IEEE CNF

22. Impact of NH_3 pre-treatment on the electrical and reliability characteristics of ultra thin hafnium silicate films prepared by re-oxidation method

Gopalan, S.; Choi, R.; Onishi, K.; Nieh, R.; Kang, C.S.; Cho, H.-J.; Krishnan, S.; Lee, J.C.;
Device Research Conference, 2002. 60th DRC. Conference Digest
24-26 June 2002 Page(s):195 - 196

IEEE CNF

23. Improved thermal stability and device performance of ultra-thin ($\text{EOT} < 10 \text{ \AA}$) gate dielectric MOSFETs by using hafnium oxynitride (HfO_xN_y)

Chang Seok Kang; Cho, H.-J.; Onishi, K.; Choi, R.; Nieh, R.; Gopalan, S.; Krishnan, S.; Lee, J.C.;
VLSI Technology, 2002. Digest of Technical Papers. 2002 Symposium on
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IEEE CNF

24. Group IVB metal oxides high permittivity gate insulators deposited from anhydrous metal nitrates

Tiezhong Ma; Campbell, S.A.; Smith, R.; Hoilien, N.; Boyong He; Gladfelter, W.L.; Hobbs, C.; Buchanan, D.; Taylor C.; Gribelyuk, M.; Tiner, M.; Coppel, M.; Jang Jung Lee;
Electron Devices, IEEE Transactions on
Volume 48, Issue 10, Oct. 2001 Page(s):2348 - 2356

IEEE JNL

25. Reliability evaluation of HfSiON gate dielectric film with 12.8 \AA SiO_2 equivalent thickness

Shanware, A.; McPherson, J.; Visokay, M.R.; Chambers, J.J.; Rotondaro, A.L.P.; Bu, H.; Bevan, M.J.; Khamankar, Colombo, L.;
Electron Devices Meeting, 2001. IEDM Technical Digest. International
2-5 Dec. 2001 Page(s):6.6.1 - 6.6.4

IEEE CNF

- 9. Characteristics of TaN gate MOSFET with ultrathin hafnium oxide (8 Å-12 Å)**
Byoung Hun Lee; Choi, R.; Kang, L.; Gopalan, S.; Nieh, R.; Onishi, K.; Jeon, Y.; Wen-Jie Qi; Kang, C.; Lee, J.C.;
Electron Devices Meeting, 2000. IEDM Technical Digest. International
10-13 Dec. 2000 Page(s):39 - 42
IEEE CNF
- 10. High-quality ultra-thin HfO₂ gate dielectric MOSFETs with TaN electrode and nitridation surface preparation**
Rino Choi; Chang Seok Kang; Byoung Hun Lee; Onishi, K.; Nieh, R.; Gopalan, S.; Dharmarajan, E.; Lee, J.C.;
VLSI Technology, 2001. Digest of Technical Papers. 2001 Symposium on
12-14 June 2001 Page(s):15 - 16
IEEE CNF
- 11. 80 nm poly-Si gate CMOS with HfO₂ gate dielectric**
Hobbs, C.; Tseng, H.; Reid, K.; Taylor, B.; Dip, L.; Hebert, L.; Garcia, R.; Hegde, R.; Grant, J.; Gilmer, D.; Franke, A.
Dhandapani, V.; Azrak, M.; Prabhu, L.; Rai, R.; Bagchi, S.; Conner, J.; Backer, S.; Dumbuya, F.; Nguyen, B.; Tobin, P.;
Electron Devices Meeting, 2001. IEDM Technical Digest. International
2-5 Dec. 2001 Page(s):30.1.1 - 30.1.4
IEEE CNF
- 12. Preliminary investigation of hafnium oxide deposited via atomic layer chemical vapor deposition (ALCVD)**
Conley, J.F., Jr.; Ono, Y.; Tweet, D.J.; Zhuang, W.; Khaizer, M.; Solanki, R.;
Integrated Reliability Workshop Final Report, 2001. 2001 IEEE International
15-18 Oct. 2001 Page(s):11 - 15
IEEE CNF
- 13. Improved film growth and flatband voltage control of ALD HfO/sub 2/ and Hf-Al-O with n/sup +/- poly-Si gate using chemical oxides and optimized post-annealing**
Wilk, G.D.; Green, M.L.; Ho, M.-Y.; Busch, B.W.; Sorsch, T.W.; Klemens, F.P.; Brijs, B.; van Dover, R.B.; Kornblit, A.
Gustafsson, T.; Garfunkel, E.; Hillenius, S.; Monroe, D.; Kalavade, P.; Hergenrother, J.M.;
VLSI Technology, 2002. Digest of Technical Papers. 2002 Symposium on
11-13 June 2002 Page(s):88 - 89
IEEE CNF
- 14. The radiation response of the high dielectric-constant hafnium oxide/silicon system**
Kang, A.Y.; Lenahan, P.M.; Conley, J.F., Jr.;
Nuclear Science, IEEE Transactions on
Volume 49, Issue 6, Dec. 2002 Page(s):2636 - 2642
IEEE JNL
- 15. Atomic scale effects of zirconium and hafnium incorporation at a model silicon/silicate interface by first principles calculations**
Kawamoto, A.; Jameson, J.; Griffin, P.; Kyeongjae Cho; Dutton, R.;
Electron Device Letters, IEEE
Volume 22, Issue 1, Jan. 2001 Page(s):14 - 16
IEEE JNL
- 16. Electrical characteristics of highly reliable ultrathin hafnium oxide gate dielectric**
Laegu Kang; Byoung Hun Lee; Wen-Jie Qi; Yongjoo Jeon; Nieh, R.; Gopalan, S.; Onishi, K.; Lee, J.C.;
Electron Device Letters, IEEE
Volume 21, Issue 4, April 2000 Page(s):181 - 183
IEEE JNL
- 17. Ultrathin hafnium oxide with low leakage and excellent reliability for alternative gate dielectric application**
Byoung Hun Lee; Laegu Kang; Wen-Jie Qi; Renee Nieh; Yongjoo Jeon; Katsunori Onishi; Lee, J.C.;
Electron Devices Meeting, 1999. IEDM Technical Digest. International
5-8 Dec. 1999 Page(s):133 - 136